

**Списък на публикациите  
на доц. дфзн Веселин Тодоров Дончев**

**включени в конкурс за получаване на академичната длъжност „Професор“**

F - Публикации в списания с IF – 16 бр.

K - Публикации в сборници на конференции – 6 бр.

(в скоби са номерата на публикациите в общия списък – файл 10A.AllPublications.pdf)

- F1 (A50) **Vesselin Donchev**, Davide Regaldo, Stefan Georgiev, Aleksandra Bojar, Mattia da Lisca, Kiril Kirilov, José Alvarez, Philip Schulz, and Jean-Paul Kleider  
*Surface Photovoltage Study of Metal Halide Perovskites Deposited Directly on Crystalline Silicon*  
ACS Omega **8** (9) 8125–8133 (2023)
- F2 (A48) Aleksandra BOJAR, Davide Regaldo, José Alvarez, David Alamarguy, **Vesselin Donchev**, Stefan Georgiev, Philip Schulz and Jean-Paul Kleider  
*Surface photovoltage characterisation of metal halide perovskite on crystalline silicon using Kelvin probe force microscopy and metal-insulator-semiconductor configuration*  
EPJ Photovoltaics **13**, 18 (2022)
- F3 (A39) M. Milanova, **V. Donchev**, K. Kostov, D. Alonso-Álvarez, E. Valcheva, K. Kirilov, I. Asenova, I. G. Ivanov, S. Georgiev and N. Ekins-Daukes  
*Experimental study of the effect of local atomic ordering on the energy band gap of melt grown InGaAsN alloys*  
Semicond. Sci, Technol. **32** (8) 085005 (2017)
- F4 (A47) **V. Donchev**, M. Milanova, K. Kirilov, S. Georgiev, K.L. Kostov, G.M. Piana, G. Avdeev,  
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J. Cryst. Growth, **574**, 126335, (2021)
- F5 (A49) **Vesselin Donchev**, Malina Milanova, Stefan Georgiev  
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Energies **15** (18) 6563 (2022)
- F6 (A22) E. S. Moskalenko, K. F. Karlsson, **V. Donchev**, P. O. Holtz, B. Monemar, W. V. Schoenfeld, P.M.Petroff  
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- F7 (A23) E. S. Moskalenko, K. F. Karlsson, **V. Donchev**, P. O. Holtz, B. Monemar, W. V. Schoenfeld, P.M.Petroff  
*Effective optical manipulation of the charge state and emission intensity of the InAs/GaAs quantum dots by means of additional infrared illumination*  
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- F8 (A26) E.S. Moskalenko, K.F. Karlsson, **V. Donchev**, P.O. Holtz, B. Monemar, W.V. Schoenfeld, P.M. Petroff  
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- F9 (A27) Evgenii S. Moskalenko, Fredrik K. Karlsson, **Vesselin T. Donchev**, Per Olof Holtz, Bo Monemar, Winston V. Schoenfeld, and Pierre M. Petroff  
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- F10 (A28) **V. Donchev**, E.S. Moskalenko, K.F. Karlsson, P.O. Holtz, B. Monemar, W.V. Schoenfeld, J.M.Garcia, P.M. Petroff  
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- F11 (A36) **V. Donchev**, D. Nesheva, D. Todorova, K. Germanova, E. Valcheva  
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- K1 (C36) **V. Donchev**, D. Todorova, E. Valcheva, Ts. Ivanov, D. Nesheva  
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- K2 (C38) D. Todorova, **V. Donchev**, D. Nesheva, E. Valcheva  
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- F12 (A37) T. Angelova, N. Shtinkov, Ts. Ivanov, **V. Donchev**, A. Cantarero, Ch. Deneke, O. G. Schmidt, and A. Cros  
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- F13 (B17) M. Saraydarov, **V. Donchev**, K. Germanova and K. Kirilov  
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- K4 (C32) K. Kirilov, **V. Donchev**, M. Saraydarov, K. Germanova  
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- K5 (C35) **V. Donchev**, K. F. Karlsson, K. Kirilov, Ts. Ivanov, K. Germanova, M. Saraydarov  
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- F15 (B18) K. Kirilov, **V. Donchev**, Tsv. Ivanov, K. Germanova, P. Vitanov and P. Ivanov  
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- F16 (B24) S. Dimitrov, E. Valcheva, **V. Donchev**  
*Electronic states properties in GaN/Al<sub>x</sub>Ga<sub>1-x</sub>N heterostructures with graded interfaces*  
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- K6 (C41) N. S. Beattie, P. See, G. Zoppi, P. M. Ushasree, M. Duchamp, I. Farrer, **V. Donchev**, D. A. Ritchie, and S. Tomic  
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